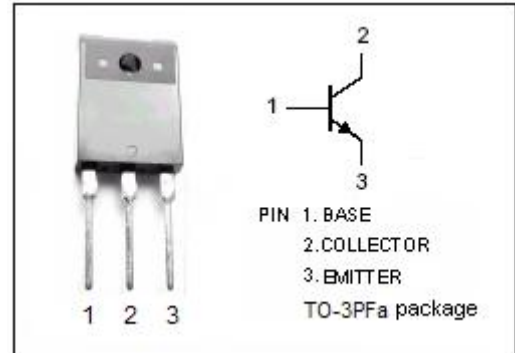


**isc Silicon NPN Power Transistor**
**2SC3577**
**DESCRIPTION**

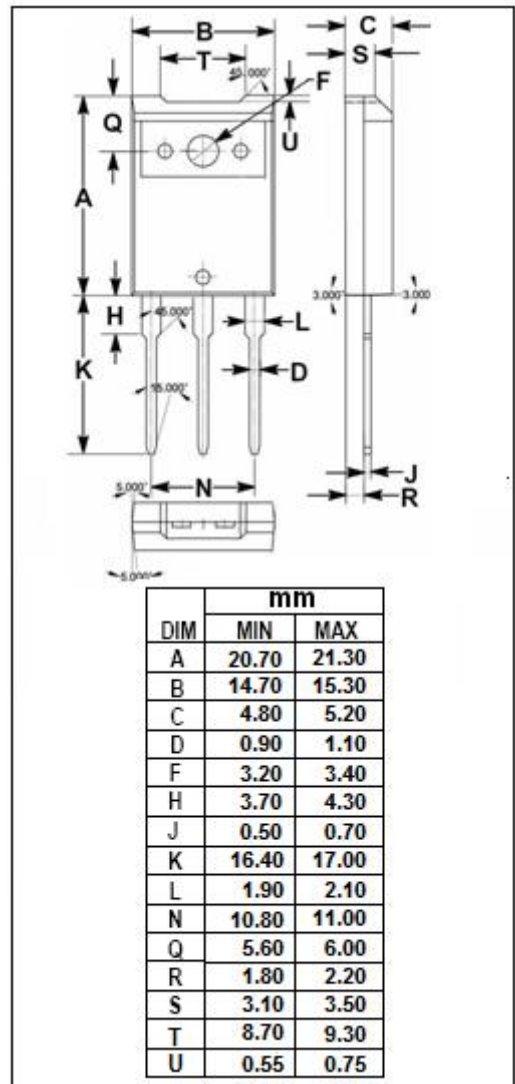
- High Collector-Base Breakdown Voltage-  
:  $V_{(BR)CBO} = 850V(\text{Min})$
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for switching regulator and high voltage switching applications.


**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	850	V
$V_{CEO}$	Collector-Emitter Voltage	650	V
$V_{EBO}$	Emitter-Base voltage	7	V
$I_C$	Collector Current-Continuous	5	A
$I_{CM}$	Collector Current-Peak	10	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	80	W
	Collector Power Dissipation @ $T_a = 25^\circ\text{C}$	3	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



## isc Silicon NPN Power Transistor

2SC3577

## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 20mA ; I <sub>B</sub> = 0	650			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; V <sub>BE</sub> = 0			50	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			50	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 10mA; V <sub>CE</sub> = 5V	10			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 5V	6			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V; f= 1MHz		6		MHz

## Switching times

t <sub>on</sub>	Turn-On Time	I <sub>C</sub> = 3A; I <sub>B1</sub> = 0.6A, I <sub>B2</sub> = -1.2A; V <sub>CC</sub> = 250V			1.0	μ s
t <sub>stg</sub>	Storage Time				2.5	μ s
t <sub>f</sub>	Fall Time				0.5	μ s

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